

# STPS40100HR

# Aerospace 2 x 20 A - 100 V

Schottky rectifier

Datasheet - production data

### **Features**

- Forward current: 2 x 20 A
- Repetitive peak voltage: 100 V
- Low forward voltage drop: 0.9 V
- Maximum junction temperature: 175 °C
- Negligible switching losses
- Low capacitance
- High reverse avalanche surge capability
- Hermetic packages
- ESCC qualified

### Description

This power Schottky rectifier is designed and packaged to comply with the ESCC5000 specification for aerospace products. Housed in hermetically sealed surface mount and through hole packages, it is ideal for use in applications for aerospace and other harsh environments.

The STPS40100HR is intended for use in medium voltage application and particularly, in high frequency circuits where low switching losses and low noise are required.

### Table 1. Device summary

Order code	ESCC detailed specification	Quality level	Package	I <sub>F (AV)</sub>	V <sub>RRM</sub>	T <sub>j</sub> (max)	V <sub>F</sub> (max)
STPS40100C2FY1	-	Engineering model	TO-254	2 x 20	100	175	0.9
STPS40100C2FYT	5106/019/05	ESCC flight					

This is information on a product in full production.



1 Characteristics

Symbol	Characteristic	Value	Unit
I <sub>FSM</sub>	Forward surge current (per diode) <sup>(1)</sup>	300	А
$V_{RRM}$	Repetitive peak reverse voltage <sup>(2)</sup>	100	V
I <sub>RRM</sub>	Repetitive peak reverse current <sup>(3)</sup>	1	А
Ι <sub>ο</sub>	Average output rectified current (50% duty cycle): <sup>(4)</sup> , <sup>(5)</sup> per diode per device	20 40	A
$I_{F(RMS)}$	Forward rms current (per diode)	30	А
T <sub>OP</sub>	Operating temperature range <sup>(6)</sup> (case temperature)	-65 to +175	°C
TJ	Junction temperature	+175	°C
T <sub>STG</sub>	Storage temperature range <sup>(6)</sup>	-65 to +175	°C
T <sub>SOL</sub>	Soldering temperature: For TO-254 <sup>(7)</sup>	+260	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/µs

Table	2.	Absolute	maximum	ratings
		/		. a m go

1. Sinusoidal pulse of 10 ms duration

2. Pulsed, duration 5 ms, F = 50 Hz

3. Pulsed, duration 2  $\mu$ s, F = 1 kHz

4. For  $T_{case} \ge +132^{\circ}C$  per device and  $T_{case} \ge +148^{\circ}C$  per diode, derate linearly to 0 A at +175°C.

5. The "per device" ratings apply only when both anode terminals are tied together.

- 6. For devices with hot solder dip lead finish all testing performed at  $T_{amb}$  > +125 °C are carried out in a 100% inert atmosphere.
- 7. Duration 10 seconds maximum at a distance of not less than 1.5 mm from the device body and the same lead shall not be re-soldered until 3 minutes have elapsed.

#### Table 3. Thermal resistance

Symbol	Characteristic	Value	Unit
$R_{th(j-c)}^{(1)}$	Thermal resistance, junction to case per diode per device	1.5 1.2	°C/W

1. Package mounted on infinite heatsink



Cumbal	<u>Characteriatia</u>	MIL-STD-750	Teet conditions	Val	Units	
Symbol	Characteristic	test method	Test conditions	Min.	Max.	Units
I <sub>R1</sub>	Reverse current	4016	DC method, $V_R = 100 V$	-	30	μA
I <sub>R2</sub>		4010	DC method, V <sub>R</sub> = 50 V	-	5	μA
V <sub>F1</sub> <sup>(1)</sup>		4011	Pulse method, I <sub>F</sub> = 5 A	-	610	mV
$V_{F2}^{(1)}$	Forward voltage		Pulse method, I <sub>F</sub> = 10 A	-	730	mV
$V_{F3}^{(1)}$			Pulse method, I <sub>F</sub> = 20 A	-	900	mV
С	Capacitance	4001	V <sub>R</sub> = 10 V, F = 1 MHz	-	1	nF
Z <sub>th(j-c)</sub> <sup>(2)</sup>	$ \begin{array}{c} \mbox{Relative thermal impedance,} \\ \mbox{junction to case} \end{array} & \begin{array}{c} \mbox{I}_{H} = 15 \mbox{ to 40 A, } t_{H} = 50 \mbox{ ms} \\ \mbox{I}_{M} = 50 \mbox{ mA, } t_{md} = 100 \mbox{ \mu s} \end{array} & \begin{array}{c} \mbox{Calculate} \\ \mbox{\Delta V}_{F}^{(3)} \end{array} \\ \end{array} $			°C/W		

1. Pulse width  $\leq$  300µs, duty cycle  $\leq$  2%

2. Performed only during screening tests parameter drift values (initial measurements for HTRB), go-no-go.

3. The limits for  $\Delta VF$  shall be defined by the manufacturer on every lot in accordance with MIL-STD-750 Method 3101 and shall guarantee the  $R_{th(j-c)}$  limits specified in maximum ratings.

Table 5. Electrical measurements at high and low temperatures (per diode)
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Symbol	Characteristic	MIL-STD-750 test method	Test conditions <sup>(1)</sup>	Values		Units
Symbol	Characteristic		lest conditions.	Min.	Max.	Units
I <sub>R1</sub>	Povorco current	4016	$T_{case} = +125 (+0, -5) °C$ DC method, V <sub>R</sub> = 100 V	-	20	mA
I <sub>R2</sub>	Reverse current		$T_{case} = +125 (+0, -5) °C$ DC method, V <sub>R</sub> = 50 V	-	7.5	mA
V <sub>F2</sub> <sup>(2)</sup>		4011	$T_{case} = +125 (+0, -5) °C$ pulse method, I <sub>F</sub> = 10 A	-	660	mV
V (2)	Forward voltage		$T_{case} = +125 (+0, -5) °C$ pulse method, I <sub>F</sub> = 20 A	-	850	mV
¥ F3` ′	V <sub>F3</sub> <sup>(2)</sup>		$T_{case} = -55 (+5, -0) °C$ pulse method, I <sub>F</sub> = 20 A	-	950	mV

1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2. Pulse width  $\leq 300 \mu s, \, duty \, cycle \leq 2\%$ 



# 2 Configurations



Figure 1. Available device configuration



### 3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

### 3.1 TO-254 package information



Figure 2. TO-254<sup>(a)</sup> package outline

a. The terminal identification is specified by the device configuration. See Figure 1 for terminal connections



Dimension in millimeters Dimension in inches						
Reference	Dimension II	n millimeters	Dimension in inches			
Reference	Min.	Max.	Min.	Max.		
А	13.59	13.84	0.535	0.545		
В	13.59	13.84	0.535	0.545		
С	20.07	20.32	0.790	0.800		
D	6.3	6.7	0.248	0.264		
E	1	3.9	0.039	0.154		
ØF	3.5	3.9	0.138	0.154		
G	16.89	17.4	0.665	0.685		
Н	6.86	BSC	0.270 BSC			
ØI <sup>(1)</sup>	0.89	1.14	0.035	0.045		
J	3.81	BSC	0.150 BSC			
К	3.81	BSC	0.150 BSC			
L	12.95	14.5	0.510	0.571		
ØM	3.05 Тур.		0.120	Тур.		
N	-	0.71	-	0.028		
R1 <sup>(2)</sup>	-	1	-	0.039		
R2 <sup>(3)</sup>	1.65	Тур.	0.065			

Table 6. TO-254 package mechanical data

1. 3 locations

2. Radius of heatsink flange corner - 4 locations

3. Radius of body corner - 4 locations



## 4 Ordering information

Order code	ESCC detailed specification	Package	Lead finish	Marking	Mass	EPPL	Packing
STPS40100C2FY1			Gold	STPS40100C2FSY1 + BeO			Strip
STPS40100C2FYT	5106/019/05	TO-254	Solder dip	510601905 + BeO	10 g	Y	pack

### Table 7. Ordering information<sup>(1)</sup>

1. Contact ST sales office for information about the specific conditions for products in die form.

## 5 Revision history

Date	Revision	Changes
26-Mar-2010	1	Initial release.
19-Mar-2014	2	Updated Table 1: Device summary and Table 7: Ordering information.
15-Sep-2015	3	Update Features and Table 8. Reformatted to current standards.
23-Oct-2015	4	Updated Table 1 and Table 7.

#### Table 8. Document revision history



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